NCD8A65S

Silicon Carbide Schottky Diode

Pb-Free RoHS COMPLIANT

Voltage:	650 Volts	Current:	8 A	Package:	TO-252

Features

- NH'S Advanced Silicon Carbide Schottky Technology
- Zero Reverse Recovery
- Positive Temperature Coefficient On VF
- Extremely Fast Switching And Extremely Low Leakage Current

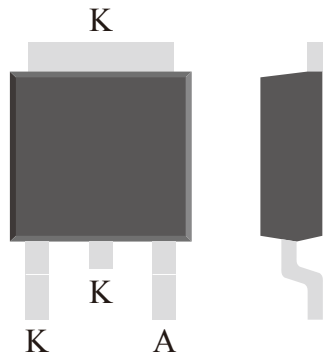
Mechanical Data

- **Case:** Molded With UL-94 ClassV-0 Recognized, RoHS-Compliant
- **Polarity:** Look At The Diagram And Polarity On The Right
- **Terminals:** Tin Plated Leads,Solderable Per J-STD-002 And JESD22-B102

Typical Applications

- Power Factor Correction (PFC)
- Unterruptible Power Supply (UPS)
- Switch Mode Power Supply (SMPS)

Diagram:



Polarity:



Maximum Ratings (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	650	V
Maximum DC Blocking Voltage		V_{DC}	650	V
Max Average Forward RectifiedCurrent	T_C= 25 ℃ T_C= 110 ℃ T_C= 150 ℃	$I_{F(AV)}$	20 11 8	A
Non-Repetitive Peak Forward Surge Current Sine Half-Wave	T_c=25°C,T_P=10ms Tc=110°C,T_P=10ms	I_{FSM}	59 49	A
Repetitive Peak Forward Surge Current Sine Half-Wave	T_C=25°C,T_P=10ms	I_{FRM}	29	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	Tc= 25 ℃ Tc= 100 ℃	P_{tot}	109 54	W
Current Squared Time	t< 8.3ms	I^2t	14.4	A^2sec
Avalanche Current,Single Pulse (Note 1)	L= 0.5 mH	I_{AS}	10	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.16	L= 0.5 mH,I_{PK}= 10.0 A Starting Tj=25 ℃,VDD = 50.0 V	E_{AS}	25	mJ

Electrical Characteristcs (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings			Unit
			Min.	Typ.	Max.	
Instaneous Forward Voltage Per Diode	Ta=25℃ I_F= 8.0 A Ta=175℃	V_F	-- --	1.38 1.67	1.66 --	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	Ta=25℃ VR=VRRM Ta=175℃ VR=80%*VRRM	I_{RRM}	-- --	0.4 2.7	26.0 --	uA
Capacitance stored energy	VR= 400 V	E_C	--	4.0	--	uJ
Total Capacitive Charge	$Qc=\int_0^{VR} C*dV$ VR= 400 V	Q_C	--	26	-	nC
Typical Junction Capacitance Per Diode	1 V,1MHz 200 V,1MHz 400 V,1MHz	C_J	-- -- --	350 53 40	-- -- --	pF

Thermal Characteristcs (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Operating Junction Temperature Range		T_J	-55 to 175	℃
Storage Temperature Range		T_{STD}	-55 to 175	℃
Max Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	$R_{\theta JC}$	1.38	℃/W

NCD8A65S

Silicon Carbide Schottky Diode

Pb Pb-Free RoHS COMPLIANT

Typical Characteristics Curves

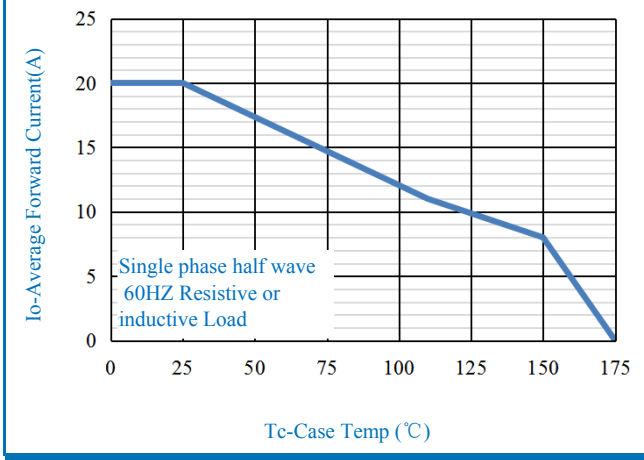


Fig.1-Forward Current Derating Curve

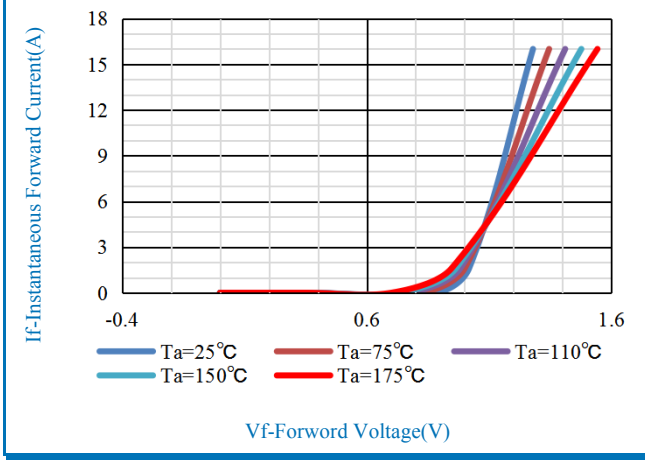


Fig.2-Typical Instantaneous Forward

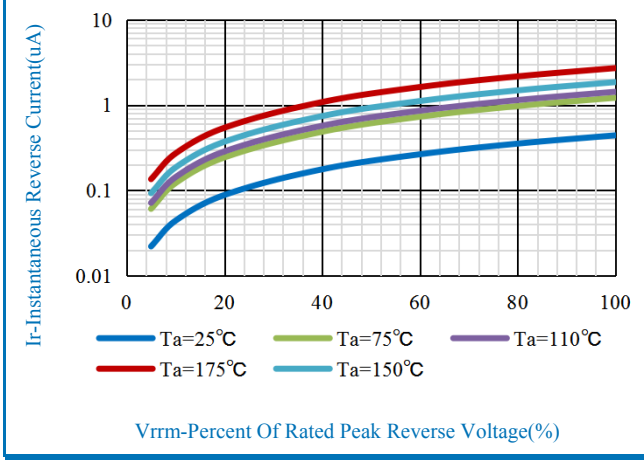


Fig.3-Typical Reverse Characteristics

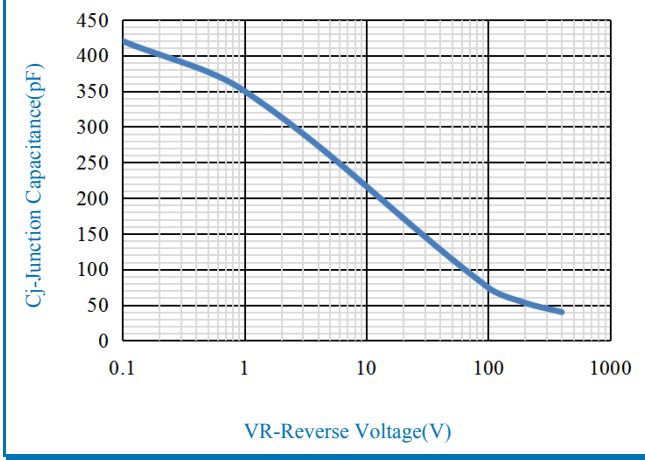


Fig.4-Typical Junction Capacitance

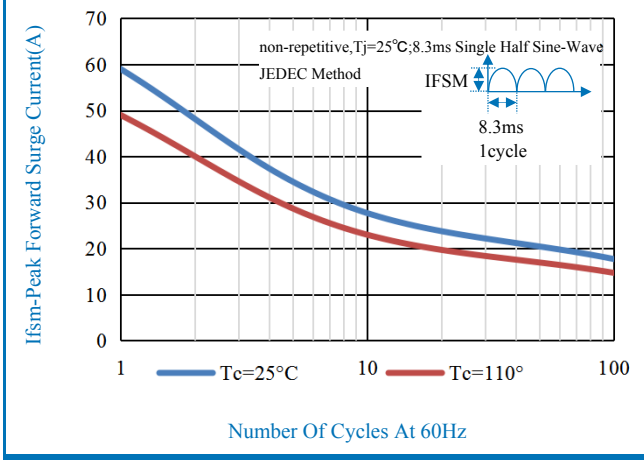


Fig.5-Max. Non-Repetitive Surge Current

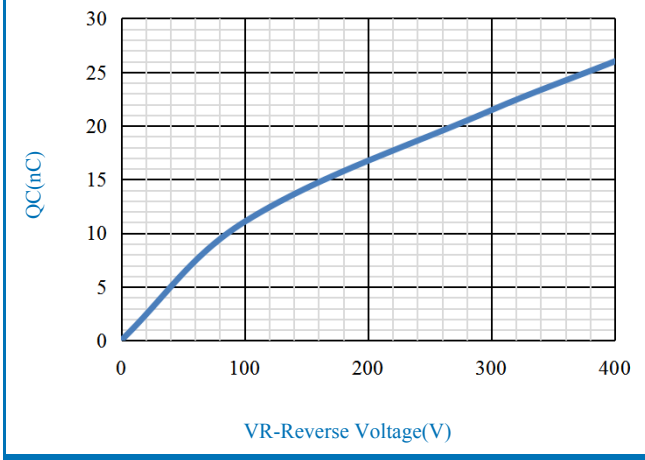


Fig.6-Total Capacitance Charge Characteristics vs. ReverseVoltage

NCD8A65S

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Pb Pb-Free RoHS COMPLIANT

Typical Characteristics Curves

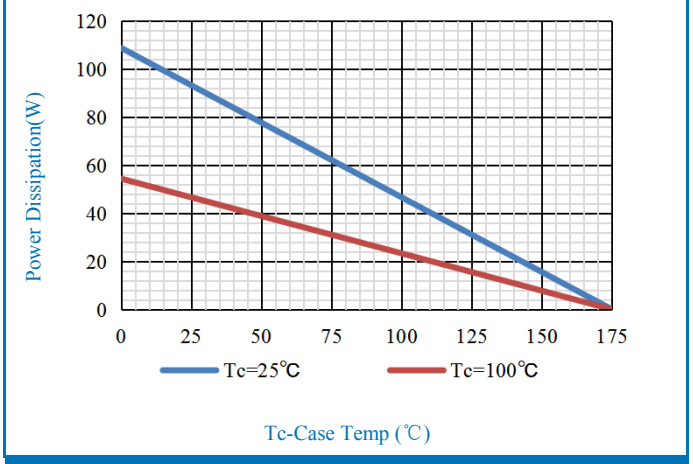


Fig.7-Power dissipation as function of case temperature

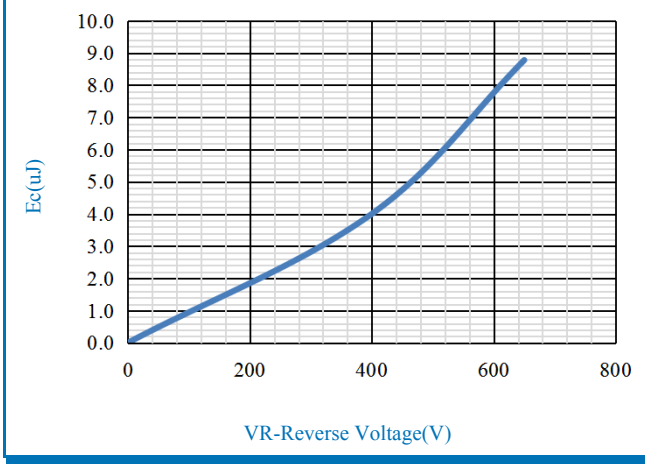


Fig.8-Capacitance Stored Energy

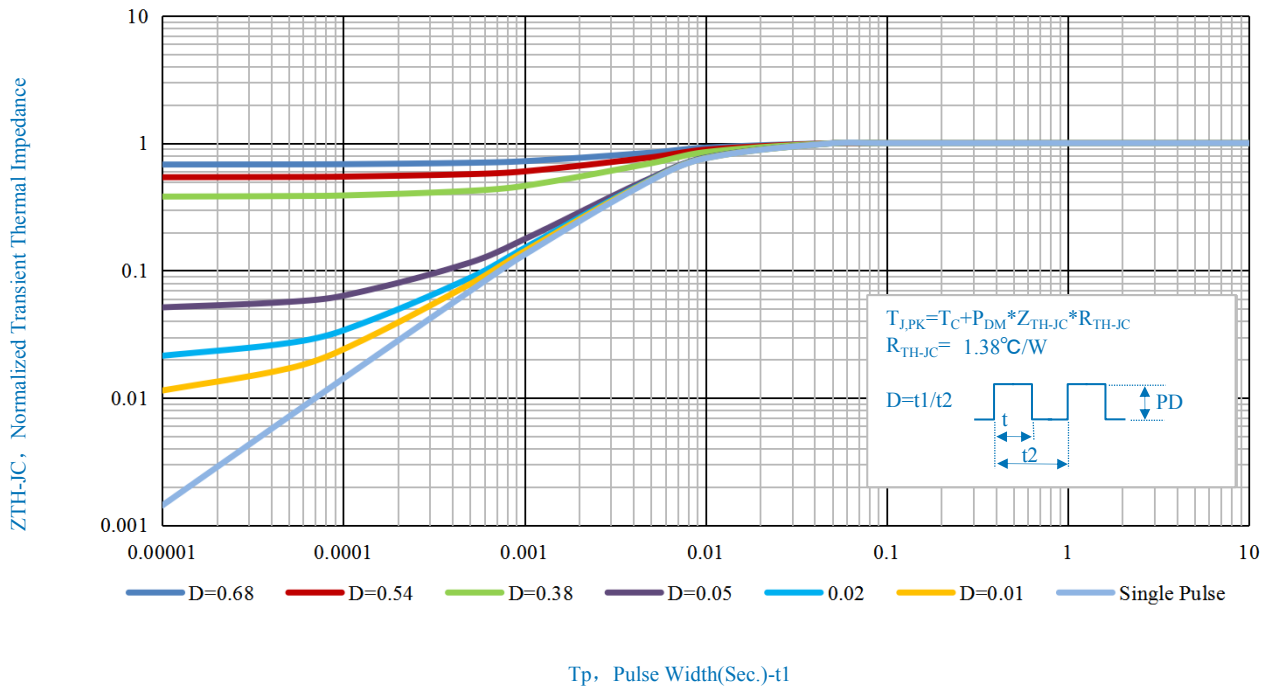


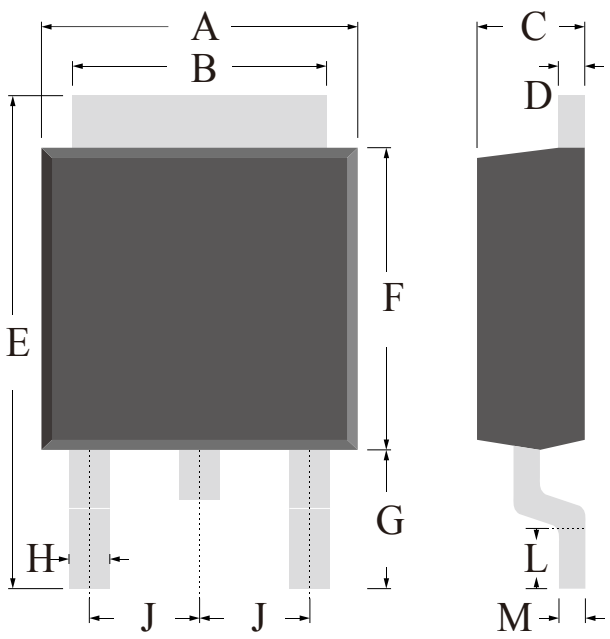
Fig.9- Normalized Maximum Transient Thermal Impedance Vs.Pulse Width

NCD8A65S

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Pb-Free RoHS COMPLIANT

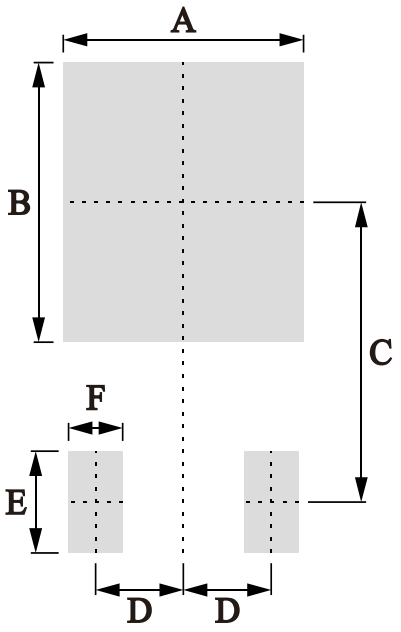
OUTLINE DRAWINGS



TO-252

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.10	-	7.10	0.2402	-	0.2795
B	4.80	-	5.80	0.1890	-	0.2283
C	1.95	-	2.55	0.0768	-	0.1004
D	0.35	-	0.75	0.0138	-	0.0295
E	9.25	-	10.75	0.3642	-	0.4232
F	5.60	-	6.60	0.2205	-	0.2598
G	2.50	-	3.10	0.0984	-	0.1220
H	0.55	-	0.85	0.0217	-	0.0335
J	2.10	-	2.50	0.0827	-	0.0984
L	1.00	-	1.40	0.0394	-	0.0551
M	0.35	-	0.75	0.0138	-	0.0295

RECOMMEDNED LAYOUT DRAWINGS



TO-252

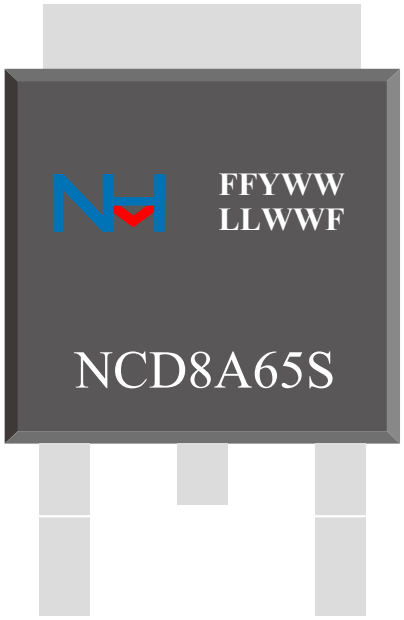
OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	6.09	-	-	0.2398	-
B	-	7.57	-	-	0.2980	-
C	-	6.64	-	-	0.2614	-
D	-	2.30	-	-	0.0906	-
E	-	2.76	-	-	0.1087	-
F	-	1.42	-	-	0.0559	-

NCD8A65S

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Pb-Free RoHS COMPLIANT

MARKING



MARKING INSTRUCTION

NH=Niuhang Trademark

FF=Product Line Code,According To Actual Changes

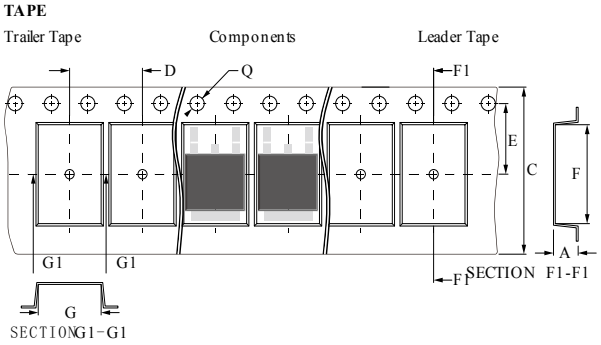
YWW=Date Code,According To Actual Changes

LLWWF=Inernal Code,According To Actual Changes

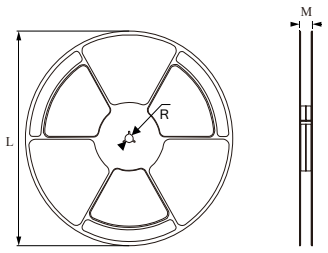
NCD8A65S=Model

PACKAGING

TAPE



REEL



TO-252

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
TAPE						
A	2.60	-	2.80	0.1024	-	0.1102
C	15.60	-	16.40	0.6142	-	0.6457
D	7.70	-	8.30	0.3031	-	0.3268
E	7.30	-	7.70	0.2874	-	0.3031
F	10.20	-	10.80	0.4016	-	0.4252
G	6.70	-	7.10	0.2638	-	0.2795
Q Φ	1.40	-	1.60	0.0551	-	0.0630
REEL						
L	328.00	-	332.00	12.913	-	13.071
R	12.00	-	14.00	0.4724	-	0.5512
M	19.40	-	23.40	0.7638	-	0.9213

PACKING INFORMATION

Package Type	Package Code	Productor Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-252	P1	0.321	13" Reel	2500	5000	30000
TO-252	P2	0.321	13" Reel	2500	2500	25000

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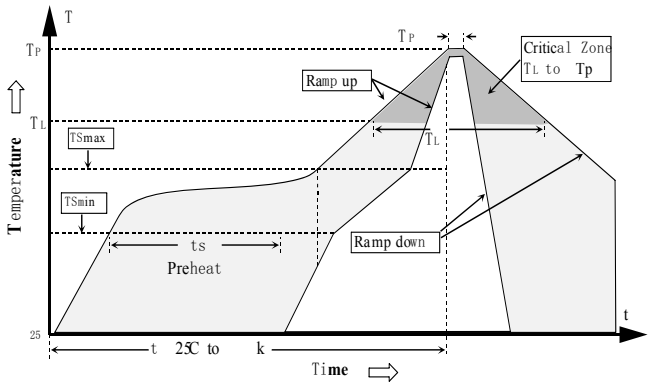
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Pb Pb-Free RoHS COMPLIANT

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat−Temperature Min (TS min) −Temperature Max (TS max) −Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature (tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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NCD8A65S

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		

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